P & N-Channel 30-V (D-S) MOSFET

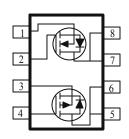
These miniature surface mount MOSFETs utilize High Cell Density process. Low r_{DS(on)} assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are PWMDC-DC converters, power management in portable and battery-powered products such as computers, printers, battery charger, telecommunication power system, and telephones power system.

syste	em, and telephones power system.
•	Low r _{DS(on)} Provides Higher Efficiency and
	Extends Battery Life

- Miniature SO-8 Surface Mount Package Saves Board Space
- High power and current handling capability
- Low side high current DC-DC Converter applications

PRODUCT SUMMARY					
$V_{DS}(V)$	$r_{DS(on)} m(\Omega)$	$I_{D}(A)$			
30	$28 @ V_{GS} = 4.5V$	7.2			
30	$18 @ V_{GS} = 10V$	8.5			
-20	$250 @ V_{GS} = -2.5V$	-2.6			
	$170 @ V_{GS} = -4.5V$	-3.2			





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)						
Parameter		Symbol	N-Channel	P-Channel	Units	
Drain-Source Voltage			30	-20	V	
Gate-Source Voltage			20	-12	V	
	T _A =25°C	T	10	-3.5		
Continuous Drain Current ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	^{1}D	7	-2.3	A	
Pulsed Drain Current ^b	I_{DM}	±50	±50			
Continuous Source Current (Diode Conduction	I_S	2.3	-2.1	A		
D Diitia	$T_A=25^{\circ}C$	D	2.1	2.1	W	
Power Dissipation ^a	$T_A=25^{\circ}C$ $T_A=70^{\circ}C$	1 D	1.3	1.3		
Operating Junction and Storage Temperature F	T_J, T_{stg}		-55 to 150	°C		

THERMAL RESISTANCE RATINGS							
Parameter	Symbol	Maximum	Units				
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	40	°C/W			
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{ heta JA}$	60	°C/W			

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Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS ($T_A =$	25°C UN	LESS OTHERWISE NO	OTED)			
Parameter	Symbol	Test Conditions	Limits			IM-	Unit
	Symbol	Test Conditions	Ch	Min	Тур	Max	Cint
Static						_	,
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{GS} = V_{DS}$, $I_D = 250 \text{ uA}$	N	1			V
	OS(III)	$V_{GS} = V_{DS}, I_D = -250 \text{ uA}$	P	-0.7		±100	
Gate-Body Leakage	I_{GSS}	$V_{GS} = -12 \text{ V}, V_{DS} = 0 \text{ V}$ $V_{GS} = 20 \text{ V}, V_{DS} = 0 \text{ V}$	N P			±100 ±100	nA
Zone Cota Waltaga Duain Comment	Ţ	$V_{DS} = -16 \text{ V}, V_{DS} = 0 \text{ V}$	P			-1	A
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 24 \text{ V}, V_{GS} = 0 \text{ V}$	N			1	uA
On-State Drain Current ^A	$I_{D(on)}$	$V_{DS} = 5 \text{ V}, V_{GS} = 10 \text{ V}$	N P	30			Α
	D(on)	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$ VGS = 10 V, ID = 8.5 A	Р	-10		18	
	ŀ	VGS = 4.5 V, I _D = 7.2 A	N			28	mΩ
Drain-Source On-Resistance ^A	$r_{DS(on)}$	VGS = -4.5 V, I _D = -3.2 A	P			170	
	•	$VGS = -2.5 \text{ V}, I_D = -2.6 \text{ A}$	1			250	Ì
Forward Tranconductance ^A	g_{fs}	$V_{DS} = 15 \text{ V}, I_{D} = 10 \text{ A}$ $V_{DS} = -15 \text{ V}, I_{D} = -9.5 \text{ A}$	N P		40 31		S
Dynamia		v _{DS} 13 v, I _D 9.3 A	Г		31		
Dynamic	1		N	1	20	1	1
Total Gate Charge	Qg	N-Channel	P		4		
	-	$V_{DS} = 15V$, $V_{GS} = 10V$, $I_{D} = 10A$	N		7		~
Gate-Source Charge	Qgs	P-Channel V _{DS} =-15V, V _{GS} =-10V, I _D =-5A	P		0.8		nC
Gate-Drain Charge	Qgd		N		7		
Gate-Dialii Charge	Qga	- , ,	P		1		
Turn-On Delay Time	td(on)	N. Channel	N		20		
Turn-on Delay Time	ta(on)	N-Chaneel	P		5		ļ
Rise Time	$t_{\rm r}$	V_{DD} =15V, V_{GS} =10V, I_{D} =1A , R_{GEN} =25 Ω , P-Channel	N P	\vdash	9		↓
			N	 	70		nS
Turn-Off Delay Time	td(off)	V _{DD} =-15V, V _{GS} =-10V, I _D =-1A	P	1	31		
Fall-Time	t_{f}	$R_{GEN}=15\Omega$	N		20		İ
ran-inic	ιi		P		28		

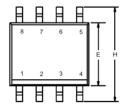
Notes

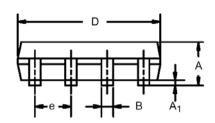
- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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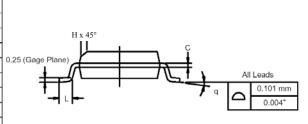
Package Information

SO-8: 8LEAD





	MILLIMETERS		INC	HES	
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27	BSC	0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0°	8°	



Ordering information

• AM4528C-T1-XX

- A: Analog Power

- M: MOSFET

– 4528: Part number

- C: Complementary

- T1: Tape & reel

– XX: Blank: Standard

PF: Leadfree

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